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Substitute for form 1449B/PTO <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  Date Submitted: January 14, 2004 <i>(use as many sheets as necessary)</i>				<b>Complete if Known</b>	
Application Number		10/757/77			
Filing Date					
First Named Inventor		J. Scott Price			
Group Art Unit					
Examiner Name					
Attorney Docket Number		070191-0362 (112019)			

U.S. PATENT DOCUMENTS						
Examiner Initials*	Cite No. <sup>1</sup>	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code <sup>2</sup> (if known)			
HKS	A1	6,333,968	B1	Whitlock et al.	12/25/2001	
	A2	6,297,592	B1	Goren et al.	10/02/2001	
	A3	5,844,216		Fathi et al.	12/01/1998	
	A4	4,289,969		Cooperstein et al.	09/15/1981	
	A5	4,012,656		Norman et al.	03/15/1977	

FOREIGN PATENT DOCUMENTS								
Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document			Name of Patentee or Applicant of Cited Documents	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>6</sup>
		Office <sup>3</sup>	Number <sup>4</sup>	Kind Code <sup>5</sup> (if known)				

NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.) date, page(s), -volume-issue number(s), publisher, city and/or country where published.	T <sup>6</sup>
HKS	A6	"Soft lithography used to fabricate transistors on curved substrates"; 3-pg. document; [obtained from Internet www.news.uiuc.edu/scitips/00/11softlitho.html]; [printed on 10/26/01].	
	A7	"Soft Lithography"; 5-pg. document; published January 1998; WTECHyper-Librarian.	
	A8	"The future of electronics manufacturing is revealed in the fine print"; Ralph G. Nuzzo; PNAS; Vol. 98, No. 9, pp. 4827-4829 (April 24, 2001).	
	A9	"Low-Temperature Fabrication of Si Thin-Film Transistor Microstructures by Soft Lithographic Patterning on Curved and Planar Substrates"; Erhardt et al.; Chemistry of Materials, Vol. 12, No. 11, pp. 3306-3315 (11/2000).	
HKS	A10	"Nucleation and growth of carbon nanotubes by microwave plasma chemical vapor deposition"; Bower et al.; Applied Physics Letters, Vol. 77, No. 17, pp. 2767-2769 (10/23/00).	

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\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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		First Named Inventor	J. Scott Price
		Group Art Unit	
		Examiner Name	
Sheet	2	of	2
		Attorney Docket Number	070191-0362 (112019)

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HPS	A11	"Large current density from carbon nanotube field emitters"; Zhu et al.; Applied Physics Letters, Vol. 75, No. 6, pp. 873-875 (8/9/99).	
	A12	"Application of carbon nanotubes as electrodes in gas discharge tubes"; Rosen et al.; Applied Physics Letters, Vol. 76, No. 13, pp. 1668-1670 (3/27/00).	
	A13	"Work functions and valence band states of pristine and Cs-intercalated single-walled carbon nanotube bundles"; Applied Physics Letters, Vol. 76, No. 26, pp. 4007-4009 (6/26/00).	
	A14	"Fabrication and Field Emission Properties of Carbon Nanotube Cathodes"; Bower et al.; 6-pg. document; Proceeding of 1999 MRS Fall Meeting.	
	A15	"10 Applications of Carbon Nanotubes"; Ajayan et al.; pp. 274-315.	
	A16	"Patterned negative electron affinity photocathodes for maskless electron beam lithography"; Schneider et al.; J. Vac. Sci. Technol.; pp. 3192-3196 (Nov/Dec 1998).	
	A17	"Semiconductor on glass photocathodes for high throughput maskless electron beam lithography"; Baum et al.; J. Vac. Sci. Technol.; pp. 2707-2712 (Nov/Dec 1998).	
HPS	A18	"Physical properties of thin-film field emission cathodes with molybdenum cones"; Spindt et al.; Journal of Applied Physics, Vol. 47, No. 12, pp. 5248-5263 (December 1976).	
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Examiner Signature	Heon Soy	Date Considered	2/15/04
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